Lam's 2300 Exelan® Demonstrates Extendibility to Sub-65 nm for Critical Front- and Backend Processes

FREMONT, Calif., June 25, 2003-Lam Research Corporation (Nasdaq: LRCX) today announced the 2300 Exelan dielectric etch system's capability for critical front- and backend sub-65-nm applications. At a number of customer sites, the system demonstrated excellent results for challenging applications, including critical front-end HARC and SAC etch and backend in situ low k dual damascene etch, validating the extendibility of Dual Frequency Confined™ (DFCTM) technology.

The 2300 Exelan achieved superior cross-wafer CD (critical dimension), etch depth, and profile control for HARC and dual damascene applications-potentially increasing the number of good die per wafer. For 65-nm gate mask open applications, the system has the capability to eliminate etch CD bias as well as compensate for lithography variations. For example, CD bias was reduced to less than 10 nm, 3 sigma, in customer tests. Exelan systems have also proven their superior process performance at the 130- and 110-nm technology nodes-validated by recent market share wins for HARC and SAC etch and continued market leadership for in situ dual damascene applications.

"This validation of Exelan's extendibility is great news for our customers who are already benefiting from the system's ability to reduce manufacturing costs significantly for current critical front- and backend applications. Now, they can leverage both their production experience and capital investment for next-generation technologies. In addition, new technologies can be introduced more rapidly because troubleshooting an unproven tool is not required," stated Jeff Marks, vice president of Dielectric Etch at Lam.

The 65-nm technology node requires tighter CD control, improved particle performance, and integration of new materials. Exelan's DFC plasma technology meets these challenges by providing two frequencies for process flexibility and a confined plasma combined with in situ Waferless AutoCleans™ to eliminate memory effects. Together, these capabilities enable the in situ processing capability pioneered by Exelan systems and provide the superior process results that have made Exelan the industry's leading choice for advanced dual damascene processes.

This press release contains certain forward-looking statements which are subject to the Safe Harbor provisions of the Private Securities Litigation Reform Act of 1995. Such forward-looking statements relate to process results, future machine performance and the speed with which new technologies can be introduced. Such statements are based on current expectations and are subject to risks, uncertainties and changes in condition, significance, value and effect as well as other risks detailed in documents filed with the Securities and Exchange Commission, including specifically the reports on Form 10-K for the year ended June 30, 2002, and the Form 10-Q for the quarter ended March 30, 2003, which could cause actual results to vary from expectations. The company undertakes no obligation to update the information or statements made in this press release.

Lam Research Corporation is a leading supplier of wafer fabrication equipment and services to the world's semiconductor industry. Lam's common stock trades on the Nasdaq National Market under the symbol LRCX. The Company's World Wide Web address is http://www.lamrc.com.

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